

SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

Abstract of Disclosure

A method for fabricating semiconductor device includes first providing a substrate having a core region, a LNA region, a I/O region, and a PA region, forming a first gate structure on the LNA region, a second gate structure on the PA region, a third gate structure on the core region, and a fourth gate structure on the I/O region, forming an interlayer dielectric (ILD) layer on the first gate structure, the second gate structure, the third gate structure, and the fourth gate structure, and then forming a first hard mask on the first gate structure and a second hard mask on the second gate structure. Preferably, a width of the first hard mask is greater than a width of the first gate structure.

Figure 1